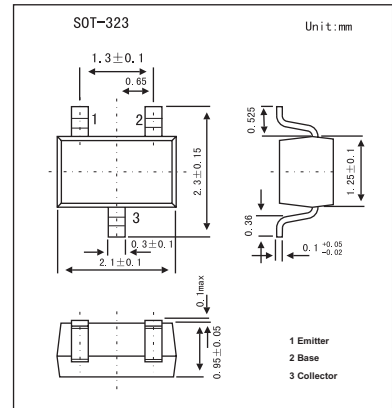


■ Features

- High transition frequency  $f_T$ .
- Small collector output capacitance  $C_{ob}$ .



■ Absolute Maximum Ratings  $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector-base voltage	$V_{CBO}$	50	V
Collector-emitter voltage	$V_{CEO}$	50	V
Emitter-base voltage	$V_{EBO}$	5	V
Collector current	$I_C$	50	mA
Collector power dissipation	$P_C$	150	mW
Junction temperature	$T_j$	150	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-55 to +150	$^\circ\text{C}$

■ Electrical Characteristics  $T_a = 25^\circ\text{C}$

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector-base voltage	$V_{CBO}$	$I_C = 10 \mu\text{A}, I_E = 0$	50			V
Collector-emitter voltage	$V_{CEO}$	$I_C = 1 \text{ mA}, I_B = 0$	50			V
Emitter-base voltage	$V_{EBO}$	$I_E = 10 \mu\text{A}, I_C = 0$	5			V
Collector cutoff current	$I_{CBO}$	$V_{CB} = 10 \text{ V}, I_E = 0$			0.1	$\mu\text{A}$
Emitter cutoff current	$I_{EBO}$	$V_{CE} = 10 \text{ V}, I_B = 0$			100	$\mu\text{A}$
Forward current transfer ratio	$h_{FE}$	$V_{CE} = 10 \text{ V}, I_C = 2 \text{ mA}$	200		500	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 10 \text{ mA}, I_B = 1 \text{ mA}$		0.06	0.30	V
Transition frequency	$f_T$	$V_{CB} = 10 \text{ V}, I_E = -2 \text{ mA}, f = 200 \text{ MHz}$		250		MHz
Collector output capacitance	$C_{ob}$	$V_{CB} = 10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$		1.5		pF

■  $h_{FE}$  Classification

Marking	AM	
	Q	R
$h_{FE}$	200~400	250~500